



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Toshimitsu Taniguchi et al. Art Unit : 2825
 Serial No. : 09/891,580 Examiner : Igwe U. Anya
 Filed : June 26, 2001
 Title : SEMICONDUCTOR DEVICE MANUFACTURING METHOD

Commissioner for Patents
 P.O. Box 1450
 Alexandria, VA 22313-1450

REPLY TO ACTION OF JUNE 19, 2003REMARKS

Claims 1-12 are pending. Claims 11 and 12 have been allowed. The applicant thank the Examiner for the allowable subject matter.

13# Response
 9/12/03
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Claim rejections – 35 USC 103

Claims 1 to 10 have been rejected as being unpatentable over Lin in view of Shimizu. It is alleged that Lin teaches everything in claims 1 and 4 except removing the oxide layer on the second device formation region along with the oxidation resistant film on the second formation region, and forming a new oxidation by thermal oxidation. However, the Examiner continues on to state that Shimizu teaches these omitted steps.

Applicant respectfully assert that that Lin, alone or in combination with Shimizu, does not teach or suggest the present invention as claimed for the following reasons.

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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